


**General Description:**

- (1) Chip Dimension  
 Chip Size = 13.8 mil x 15.8 mil (340um x 400um)  
 Chip Thickness = 90±10µm  
 P/N Bonding Pad = 100±5µm
- (2) Electrode:  
 P (Anode) → Au  
 N (Cathode) → Au

- (3) Structure:  
 Refer to drawing

**Electro-optical Characteristics (Ta=RT)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	$V_F$	2.8	-	3.5	V	$I_F=20mA$
Dominant Wavelength	$\lambda_D$	445	460	470	nm	$I_F=20mA$
Reverse Current	$I_R$	0	-	1	µA	$V_R=-5V$

Luminous Intensity( Iv ) mcd at $I_F=20mA$	Dominant Wavelength(nm)												
	Range	44C: 445~447.5	44D: 447.5~450	45A: 450~452.5	45B: 452.5~455	45C: 455~457.5	45D: 457.5~460	46A: 460~462.5	46B: 462.5~465	46C: 465~467.5	46D: 467.5~470	47A: 470~472.5	47B: 472.5~475
7: 30~40													
8: 40~50													
9: 50~60	*	*	*										
A: 60~70	*	*	*	*	*	*	*	*	*				
B: 70~80	*	*	*	*	*	*	*	*	*				
C: 80~90			*	*	*	*	*	*	*				
D: 90~100				*	*	*	*	*	*	*			
E: 100~120					*	*	*	*	*	*			
F: 120~140					*	*	*	*	*	*			
G: 140~160									*	*			
H: 160~180													
I: 180~200													
J: 200~240													
K: 240~280													

**Features:**

1. High Luminous Intensity
2. Long Operation Life
3. High Current; Pulse Operation
4. Indoor/Outdoor Applications

**Notes:**

1. Dominant wavelength includes an error of ± 1nm
2. Luminous intensity includes an error of ±10%
3. Luminous intensity is measured on bare chip
4. InGaN LED is sensitive to ESD

\* MODEL NO: SN 4XX 14A X

↳ (WLD) ↳ (Iv)